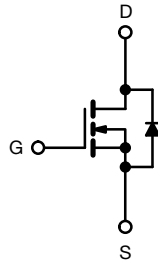


Power MOSFET

TO-220AB


N-Channel MOSFET

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche, and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective C_{oss} specified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


 Available
RoHS*
 Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptable power supply
- High speed power switching

TYPICAL SMPS TOPOLOGIES

- Two transistor forward
- Half bridge
- Full bridge

PRODUCT SUMMARY

V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.85
Q_g max. (nC)	38	
Q_{gs} (nC)	9.0	
Q_{gd} (nC)	18	
Configuration	Single	

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF840APbF
Lead (Pb)-free and halogen-free	IRF840APbF-BE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)


PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	500	V	
Gate-source voltage	V_{GS}	± 30		
Continuous drain current	V_{GS} at 10 V	$T_C = 25$ °C	8.0	A
		$T_C = 100$ °C	5.1	
Pulsed drain current ^a	I_{DM}	32		
Linear derating factor		1.0	W/°C	
Single pulse avalanche energy ^b	E_{AS}	510	mJ	
Repetitive avalanche current ^a	I_{AR}	8.0	A	
Repetitive avalanche energy ^a	E_{AR}	13	mJ	
Maximum power dissipation	$T_C = 25$ °C	P_D	125	W
Peak diode recovery dV/dt ^c		dV/dt	5.0	V/ns
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^d	For 10 s		300	
Mounting torque	6-32 or M3 screw		10	
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 16$ mH, $R_g = 25$ Ω , $I_{AS} = 8.0$ A (see fig. 12)
- $I_{SD} \leq 8.0$ A, $dI/dt \leq 100$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C
- 1.6 mm from case



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	1.0	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.58	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4.8\text{ A}^b$	-	-	0.85	Ω
Forward transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 4.8\text{ A}^b$		3.7	-	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	1018	-	pF
Output capacitance	C_{oss}			-	155	-	
Reverse transfer capacitance	C_{riss}			-	8.0	-	
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}; V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$		-	1490	-	
Output capacitance	C_{oss}	$V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$		-	42	-	
Effective output capacitance	$C_{oss\text{ eff.}}$	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ V to } 400\text{ V}^c$		-	56	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 8\text{ A}, V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^b	-	-	38	nC
Gate-source charge	Q_{gs}			-	-	9.0	
Gate-drain charge	Q_{gd}			-	-	18	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 8\text{ A}$ $R_g = 9.1\text{ }\Omega, R_D = 31\text{ }\Omega$, see fig. 10 ^b		-	11	-	ns
Rise time	t_r			-	23	-	
Turn-off delay time	$t_{d(off)}$			-	26	-	
Fall time	t_f			-	19	-	
Gate input resistance	R_g	$f = 1\text{ MHz}$, open drain		0.7	-	3.7	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	8.0	A
Pulsed diode forward current ^a	I_{SM}			-	-	32	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.0	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	422	633	ns
Body diode reverse recovery charge	Q_{rr}			-	2.16	3.24	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$
- c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

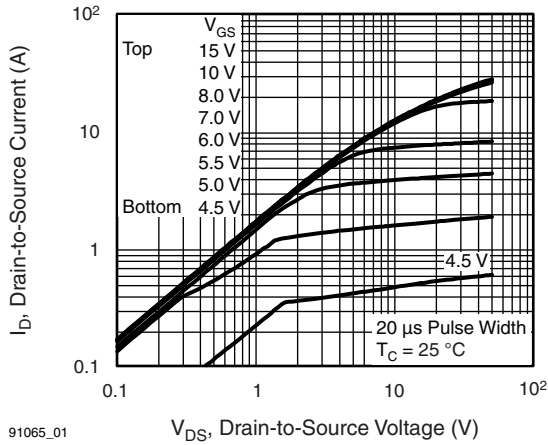


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

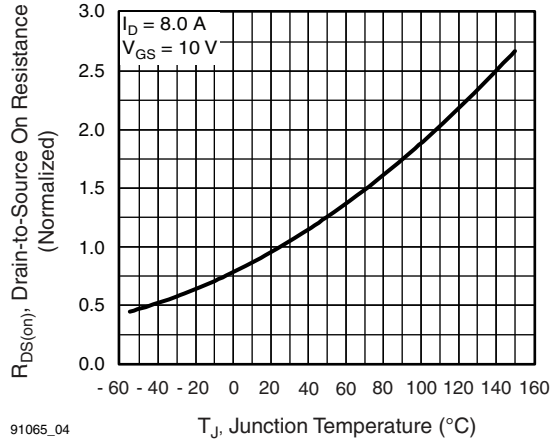


Fig. 4 - Normalized On-Resistance vs. Temperature

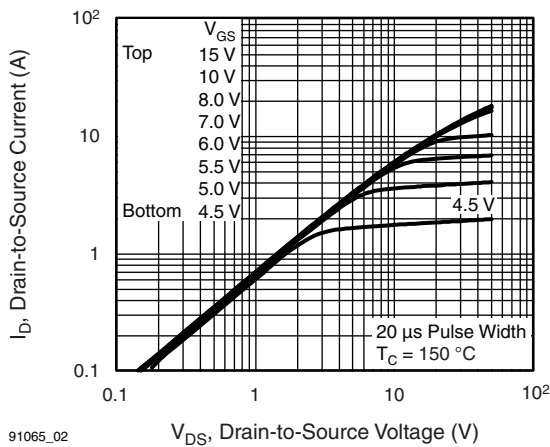


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

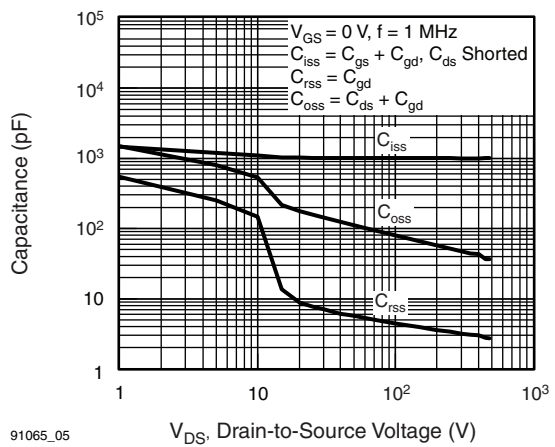


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

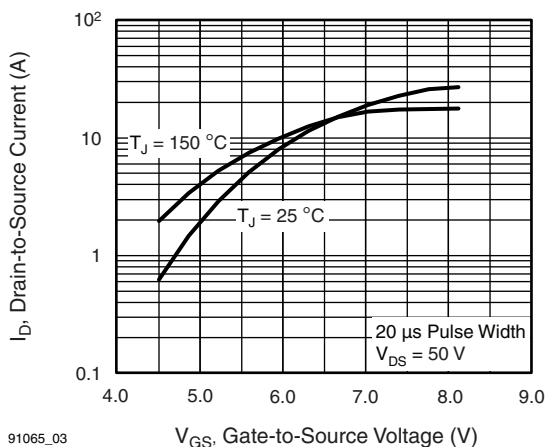


Fig. 3 - Typical Transfer Characteristics

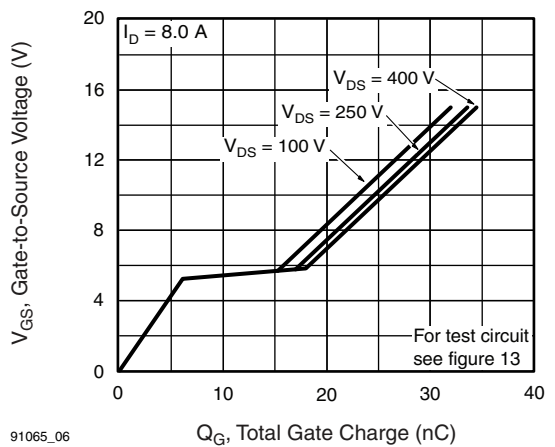
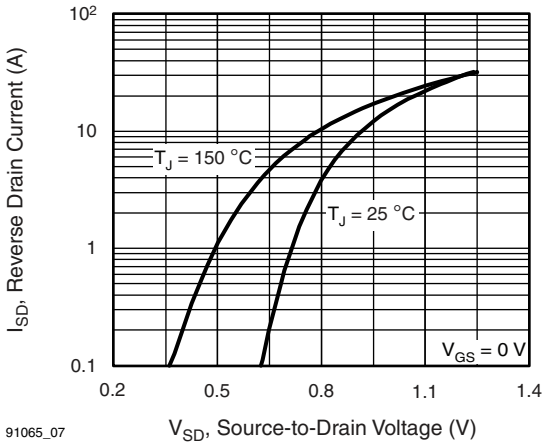
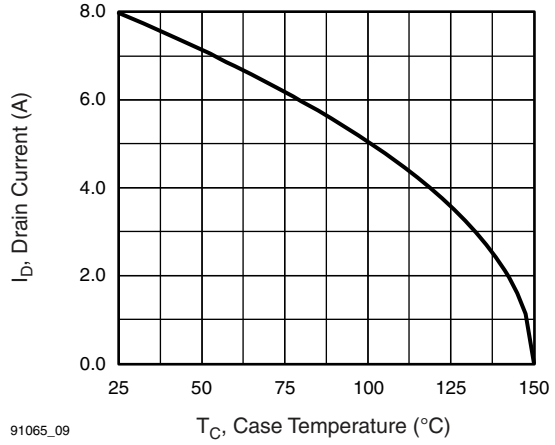


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



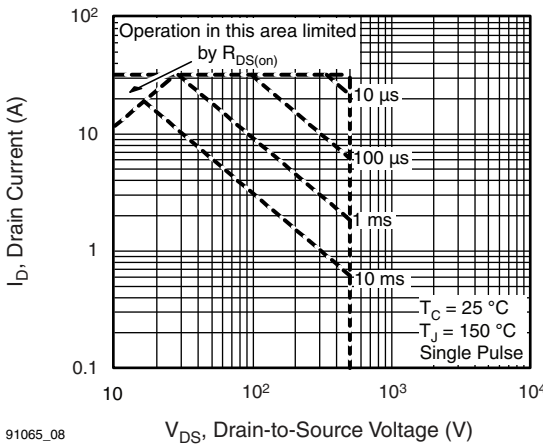
91065_07

Fig. 7 - Typical Source-Drain Diode Forward Voltage



91065_09

Fig. 9 - Maximum Drain Current vs. Case Temperature



91065_08

Fig. 8 - Maximum Safe Operating Area

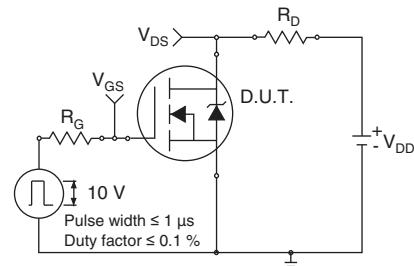


Fig. 10a - Switching Time Test Circuit

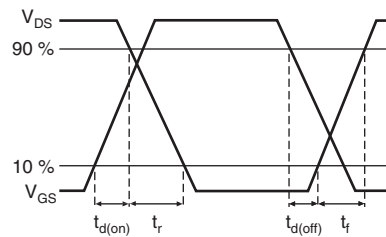
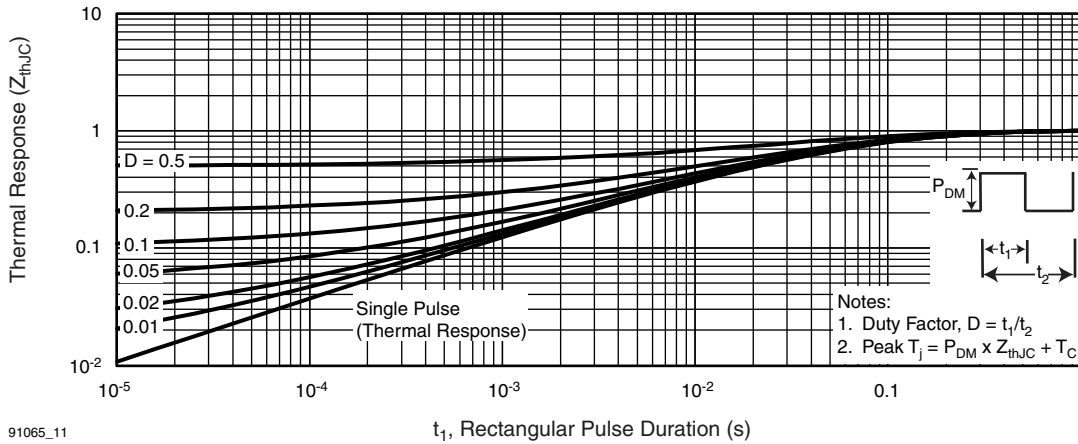


Fig. 10b - Switching Time Waveforms



91065_11

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

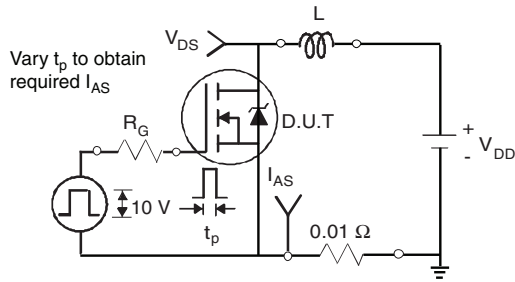


Fig. 12a - Unclamped Inductive Test Circuit

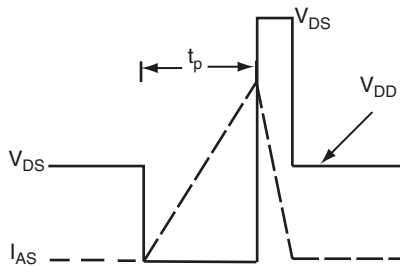
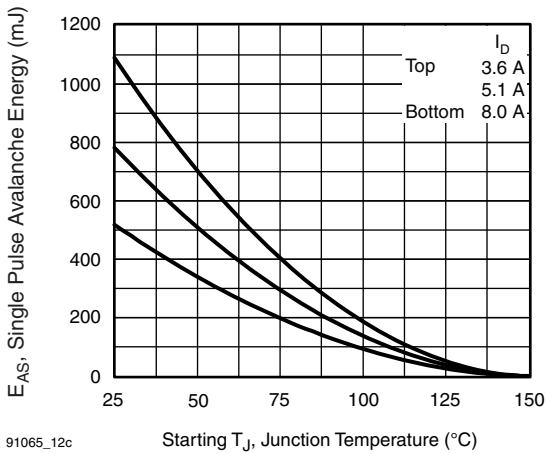


Fig. 12b - Unclamped Inductive Waveforms



91065_12c

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

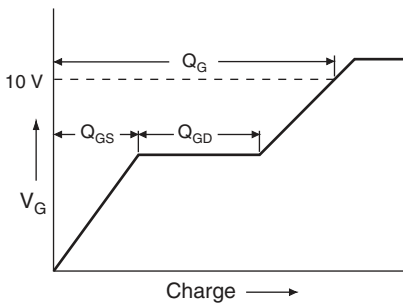
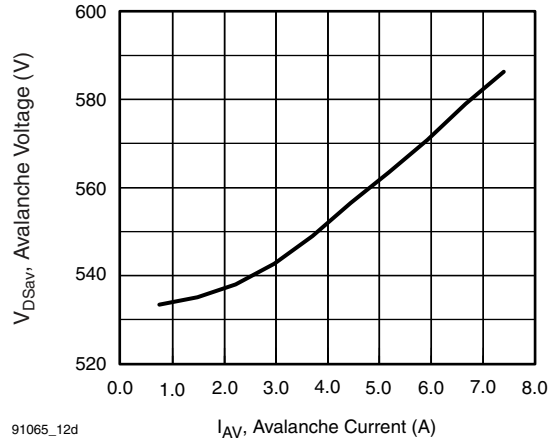


Fig. 12d - Basic Gate Charge Waveform



91065_12d

Fig. 13a - Typical Drain-to-Source Voltage vs. Avalanche Current

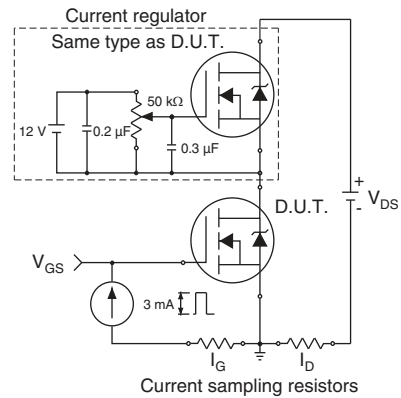
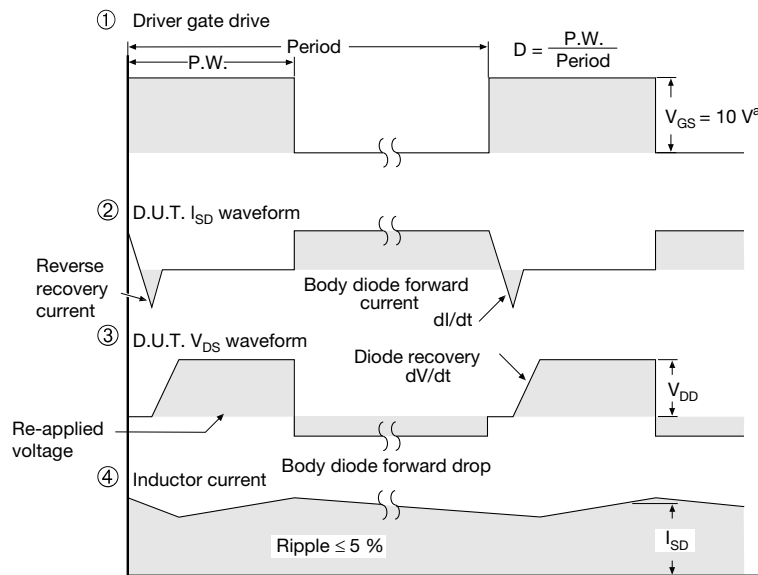
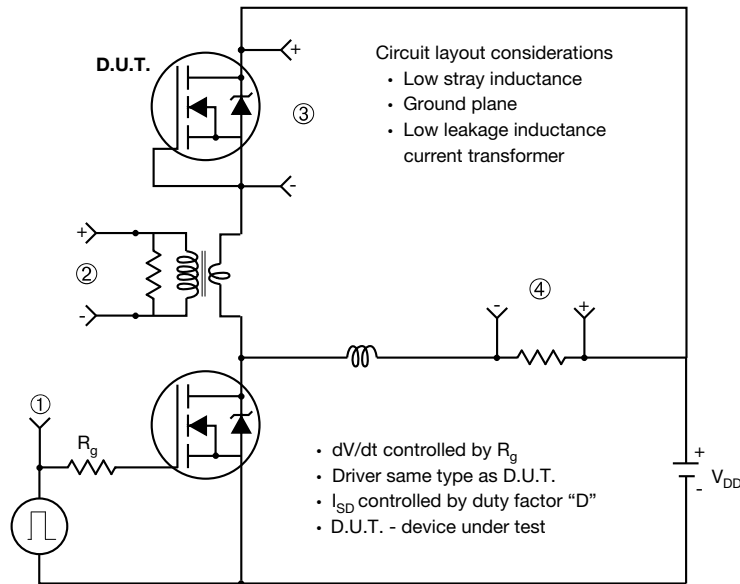


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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